EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4634	(361/56-58).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/04/20 09:55
L2	324	string near2 diodes and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L3	133	1 and 2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L4	0	(stack$3 series) near5 cascasd$2 and 3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:56
L5	112	(stack$3 series cascad $2 cascod$3) and 3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 09:57
L6	214	(stack$3 series) same cascad$2 and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 10:17
L7	690	cascad$3 and (shunt shunting clamp clamping trigger triggering triggered) and (ESD electrostatic near2 discharge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:11

L8	37	(cascaded cascade cascading) near7 stack $2 and 7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:12
L9	2316	(array divider series string) near2 diodes and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L10	0	(stack$3 series) near5 cascasd$2 and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L11	0	cascasd$2 and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L12	6	cascad$3 near4 (shunt shunting clamp clamping trigger triggering triggered) and 9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:14
L13	5641	freescale near2 semiconductor.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:29
L14	72	(cascaded cascade cascading) and 13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:29
L15	54	Yi near2 Hsun near2 Wu.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:30

L16	11	("20030076636" | "20040110334" | "20050041346" | "20050264963" | "6327126" | "6414532" | "6522511" | "6538868" | "6747857" | "6867957" | "6898062").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/04/20 11:33
L17	8	(cascaded cascade cascading) and 15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:33
L18	182	jian near2 hsing near2 lee.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:34
L19	15	(cascaded cascade cascading) and 18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:34
L20	17302	Taiwan near2 semiconductor near2 manufacturing.as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L21	739	20 and (electrostatic near2 discharge ESD electrostatic near3 energy electrostatic near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L22	45	(cascaded cascade cascading) and 21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:35
L23	1	(ESD near2 protection and sensor and inverter and cascaded near2 NMOS).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/04/20 11:38

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